

Towards Error-Free Photonic Interconnects

Jiang Xu



**BIG DATA
SYSTEM
LAB**



香港科技大學
THE HONG KONG UNIVERSITY OF
SCIENCE AND TECHNOLOGY

OPTICS Lab

Team Members

- Current PhD students

- Jun Feng, Shixi Chen, Jiaxu Zhang, Xiao Li, Lin Chen, Yinyi Liu, Yuxiang Fu, Chengeng Li, Fan Jiang, Man Lee Ho, Xianbin Li

- Past group members

- Prof. Weichen Liu, *Nanyang Technological University*
- Prof. Mahdi Nikdast, *Colorado State University*
- Prof. Sébastien Le Beux, *Concordia University*
- Prof. Yaoyao Ye, *Shanghai Jiao Tong University*
- Prof. Yiyuan Xie, *Southwest University*
- Prof. Yu Wang, *Tsinghua University*
- Prof. Huaxi Gu, *Xidian University*
- Dr. Zhongyuan Tian, *Huawei*
- Dr. Xiaowen Wu, *Huawei*
- Dr. Peng Yang, *Huawei*
- Dr. Zhe Wang, *Huawei*
- Dr. Xing Wen, *Apple*
- Dr. Rafael Maeda, *Apple*
- Dr. Xuan Wang, *HiSilicon*
- Dr. Xuanqi Chen, *HiSilicon*
- Dr. Zhehui Wang, *A*STAR*
- Dr. Haoran Li, *Alibaba Damo Academy*
- Dr. Zhifei Wang, *Electronics Technology Group*
- Dr. Duong Luan, *Nanyang Technological University*



Photonics can Complement Electronics

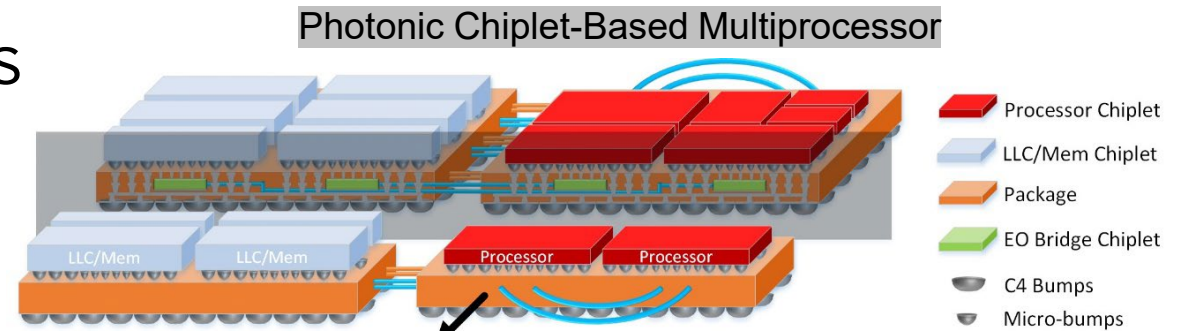
- Electronics is good for computation and memory
- Photonics is good for communications

+ Advantages

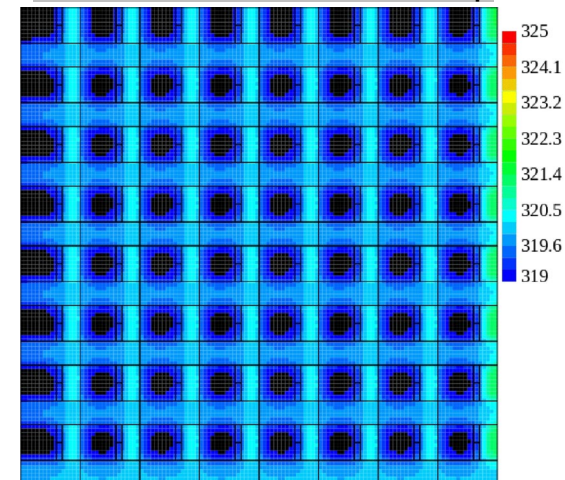
- + Ultra-high bandwidth
- + Low propagation delay
- + Low propagation loss
- + Low sensitivity to environmental EMI

- Challenges

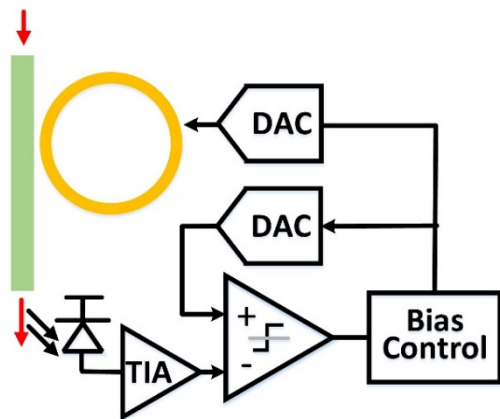
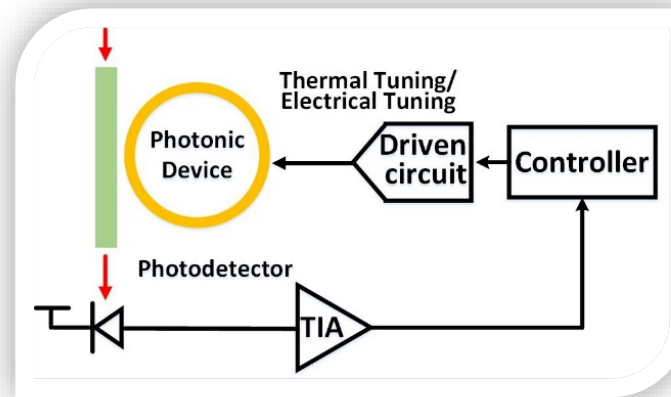
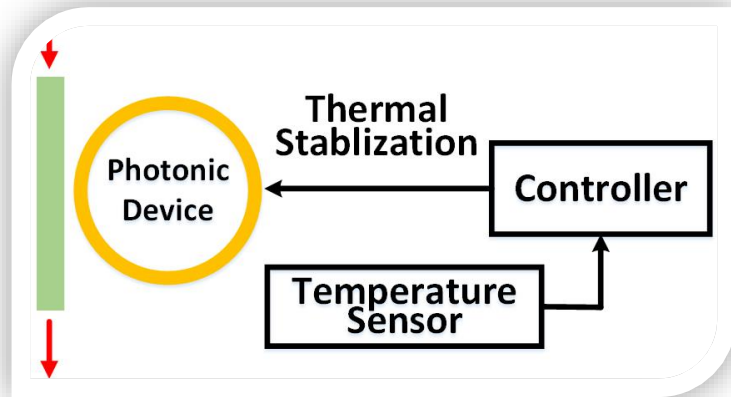
- Thermal variation -> errors and even failures
- Crosstalk noise
- Process variation
- Nonlinear effects
- Difficult to buffer
- OE conversions



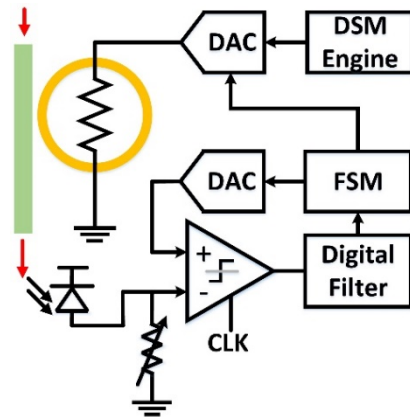
Thermal Variation on a Chip



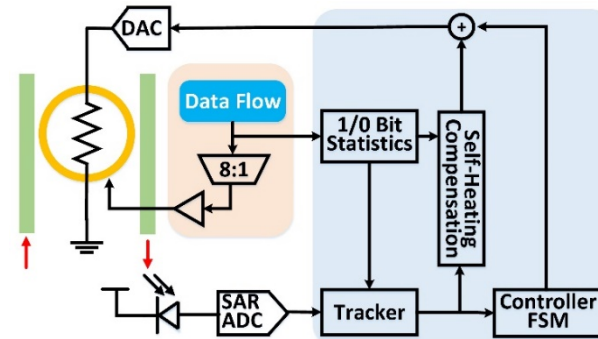
Thermal Stabilization vs. Device Turning



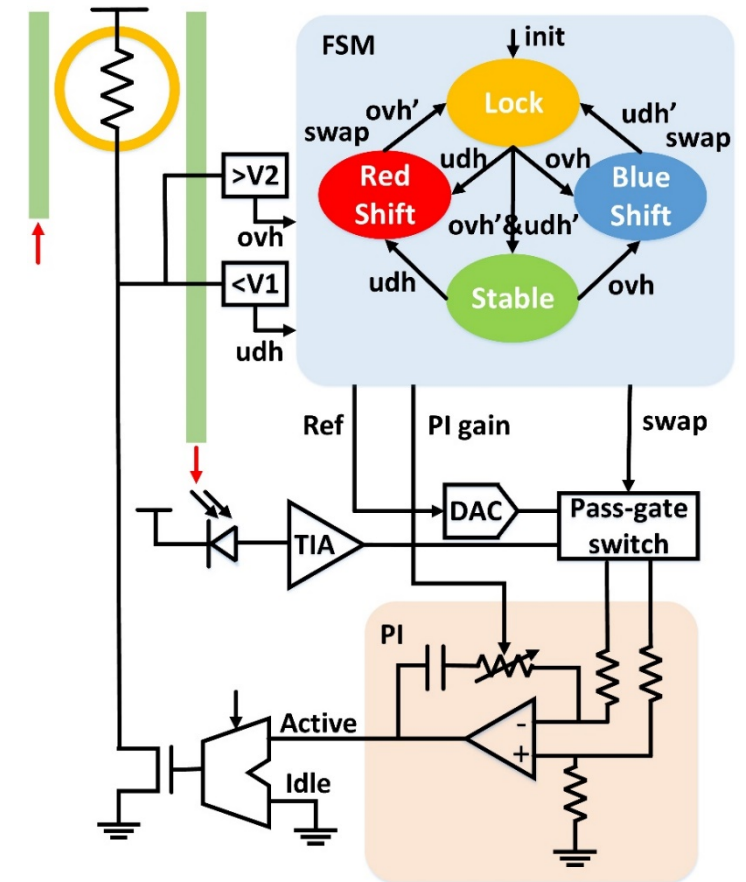
C. Li *et al*, JSSC 2014



K. Yu *et al*, ISSCC 2015



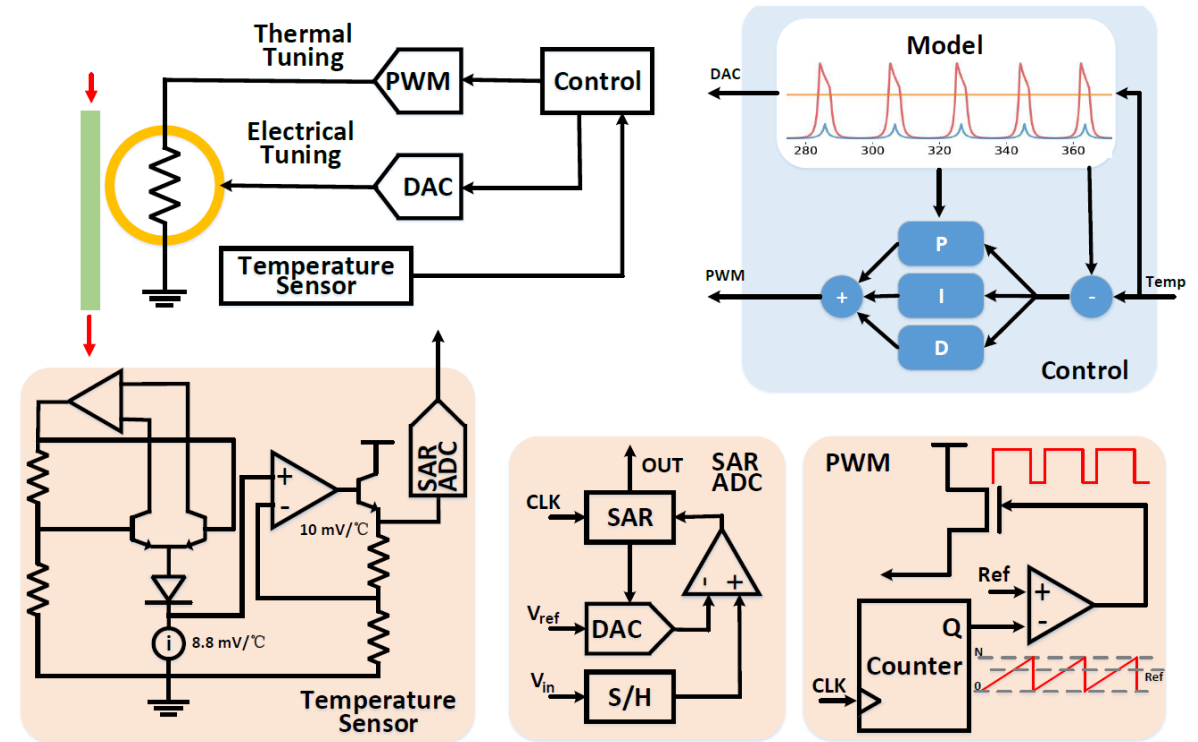
C. Sun *et al*, JSSC 2016



Y. Thonnart *et al*, ISSCC 2018

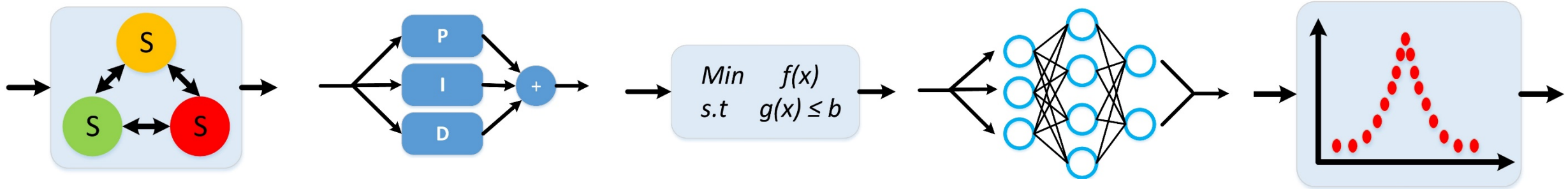
Indirect Feedback Tuning (IFT)

- Tune device characteristics based on device temperature
- Complemented electrical and thermal tuning
 - Electrical tuning is fast (ns) but has a small tuning range
 - Thermal tuning is slow (μs) but has a large tuning range
- More responsive
- Low cost and low power
- Do not need any optical port



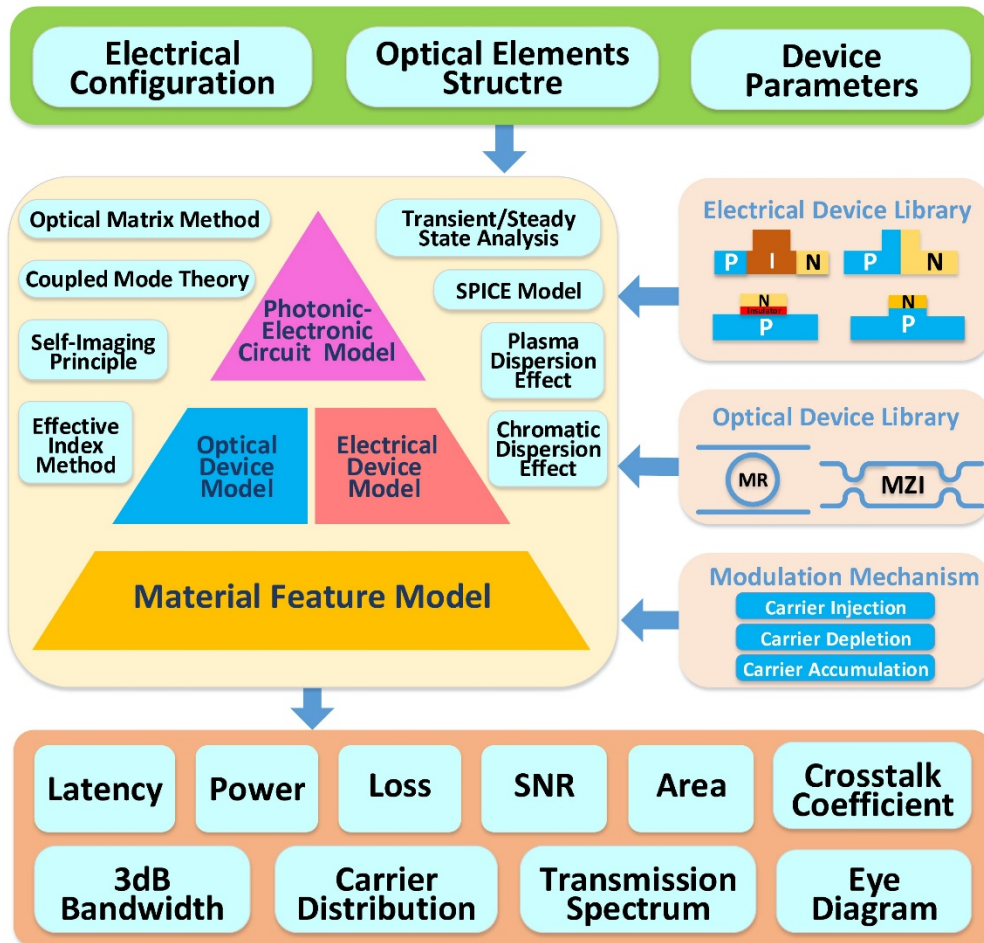
*X. Chen, *et al.* "Simultaneously Tolerate Thermal and Process Variations through Indirect Feedback Tuning for Silicon Photonic Networks," IEEE TCAD, 2020

IFT Control Logic



FSM	PID	Optimal Control	Q-Learning	Model Predictive
Pros				
HW-efficient	HW-efficient, no expertise knowledge	optimal point, cost function	Intelligent, no expertise knowledge	nonlinear control, prediction, HW-efficient,
Cons				
linear control, finite state, large granularity	linear control, oscillation issue, parameter tuning	hardware cost $O(n^{3.5})$, expertise knowledge	HW cost for large numbers of states/actions	Need a model

BOSIM is Used to Develop a Control Model



- BOSIM is a photonic device design, modeling, and simulation tool
- Validated by fabricated devices from 8 companies and institutes
- Study transit and static device characteristics
- Understand device structures and material choices
- Accelerate design exploration

<https://eexu.home.ece.ust.hk/BOSIM.html>

Component Design and System-level Simulation Setup

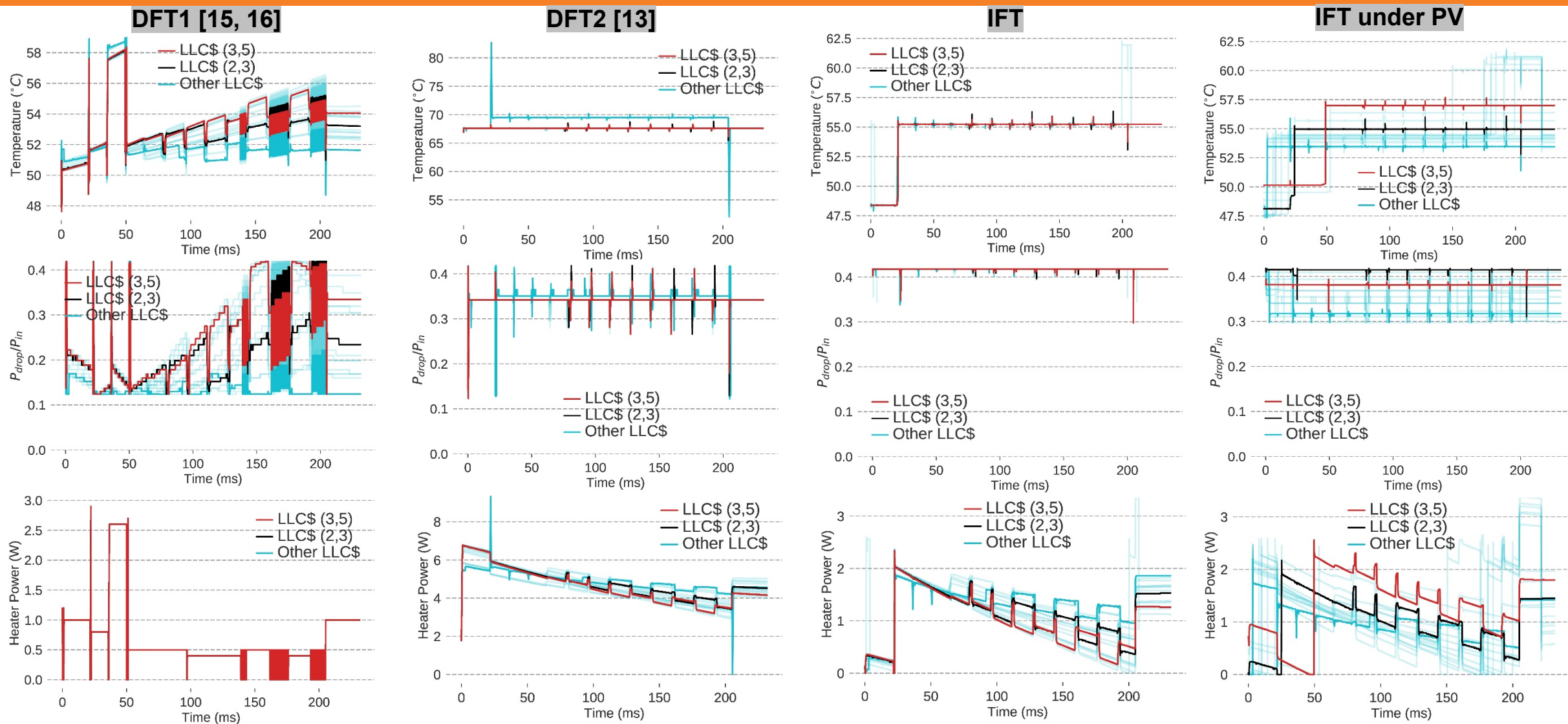
Circuit *							
	ADC	DAC	TIA	OA	Sensor [42]	PD	Calibration
Power (mW)	0.52	2.5	0.71	0.2	1.2	0.03	0.2
Area (μm^2)	183.4	138.3	123.5	123.5	48	10	183.4
Laser efficiency				0.33 [48]	Laser Extinction Ratio		10
Photodetector Sensitivity	-14.2 dBm (BER 10^{-12})[49]			Communication Band			O-Band
Switch °							
WDM channel amount	14			Ring Radius	near 10 μm		
	Phase Shifter						
Rib Width	0.4 μm			Film Height	0.4 μm		
Etching Depth	0.3 μm			Cladding Height	1.2 μm		
PN Horizontal Offset	-0.15 μm			PN Vertical Offset	0.1 μm		
	Directional Coupler						
Length	0.1 μm			Gap	0.18 μm		
	Doping						
Device Type	L-shaped PN			Modulation Mechanism	Carrier Depletaion		
P-area-NA	$1.0 \times 10^{18} cm^{-3}$			N-area-ND	$2.0 \times 10^{18} cm^{-3}$		
P-area-x	0.6 μm			N-area-x	0.6 μm		
	SPICE Model						
τ	0.5 ns			R_S Series Resistance	55 Ω		
I_S	$1.0 \times 10^{-8} \mu A$			n_{pn}	1		
V_0	1.0 V			$C_j(0)$	0.4 pF		
IBV	1000 μA			BV	40.0 V		
DC Bias	-4 V			Vpp	11 V		
	Material						
	substrate/cladding			guiding film	air		
refractive index	SiO ₂ : 1.45			Si: 3.45	1		
absorption (mm^{-1})	N.A.			0.015	N.A		
thermal diffusivity (mm^2/s)	SiO ₂ : 0.83			Si: 88	19		
permittivity ($\epsilon_0 = 8.854 \times 10^{-14}$)	$3.9\epsilon_0$			$11.7\epsilon_0$	ϵ_0		

System level simulations use

- JADE multiprocessor simulation environment
- COSMIC application benchmark suite

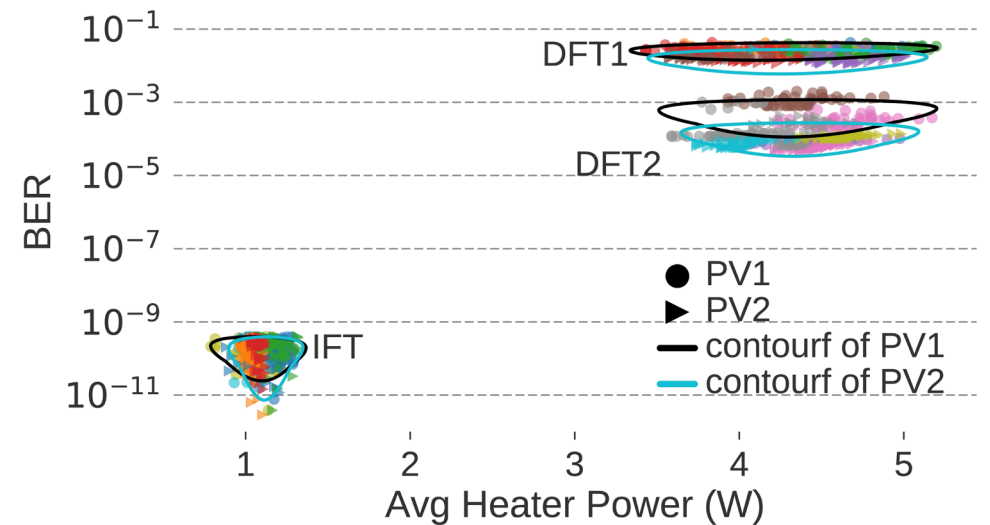
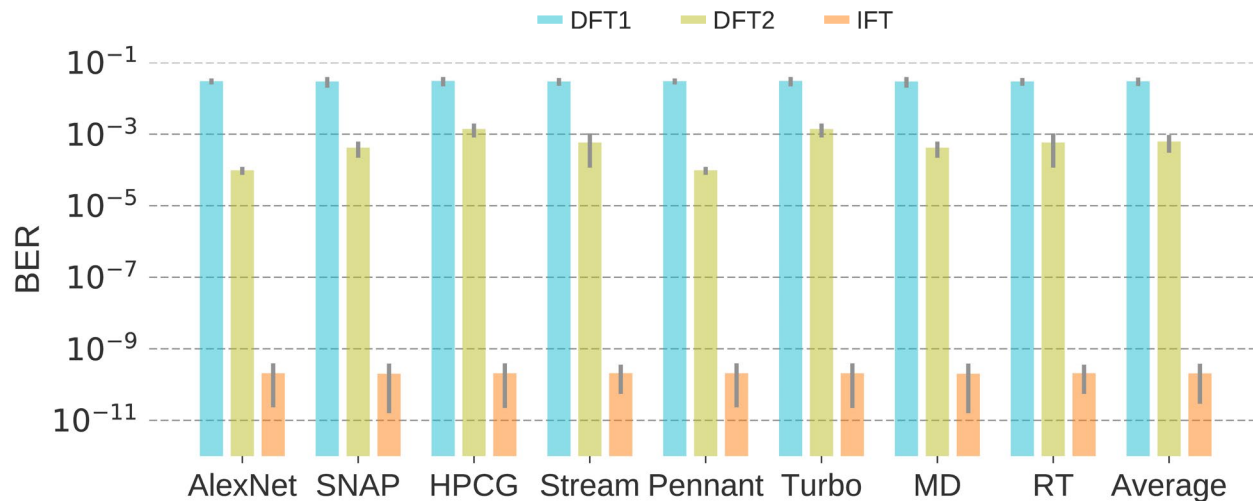
Parameter	Value	Parameter	Value		
Architecture					
Core	RISC-V, 64-Core	Working frequency	3 GHz		
Core cluster	4 core/cluster	L1 I/D cache	Private, 32 KB/Core		
L2 cache	Shared, 128 KB/Core	Coherence Protocol	Directory-based MOSI		
Cache line size	64 Byte	NoC Topology	Ring		
Variation					
wafer diameter	200 mm	chip die area	236.7 mm^2		
chip thermal threshold	354.95 K				
Process Variation †					
	linewidth	gap	film thickness	waveguide loss	dopant
noise type	Simplex	Simplex	Joint Gaussain	Simplex	Perlin
noise radius	20 mm	20 mm	N.A.	30 mm	N.A.
noise amplitude _{PV1}	2.4 nm	1 nm	2 nm	1.5 dB	$10^{17}cm^{-3}$
noise amplitude _{PV2}	1.6 nm	0.6 nm	1.2 nm	1.0 dB	$10^{17}cm^{-3}$
Thermal Variation ‡					
		silicon chip		heat sink	spreader
thermal conductivity ($W/(m \cdot K)$)		100.0		400.0	400.0
specific heat ($J/(m^3 \cdot K)$)		1.75×10^6		3.55×10^6	3.55×10^6
thickness (mm)		0.15		6.9	1.0
side (mm)		N/A		60	30
heat sink convection resistance	0.1 K/W	heat sink convection capacitance			140.4 J/K

Case Analysis: SNAP Benchmark



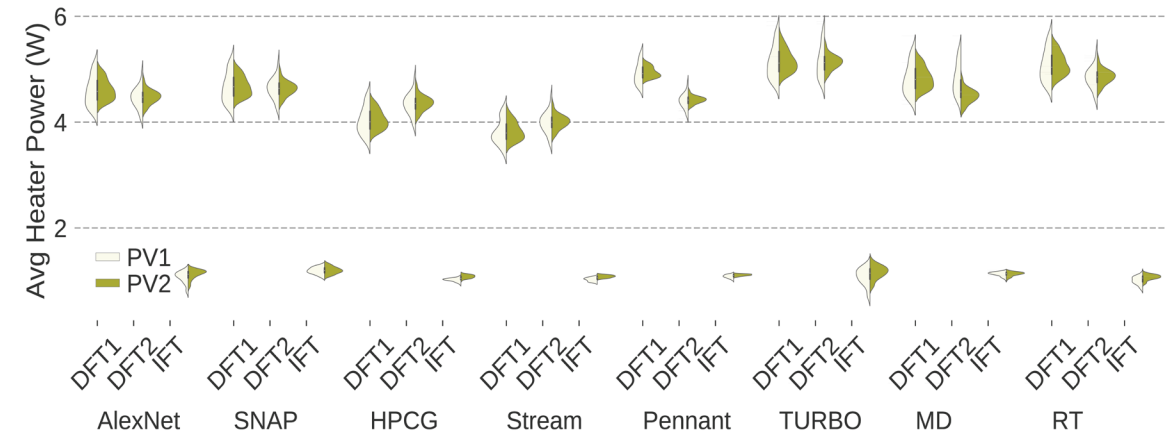
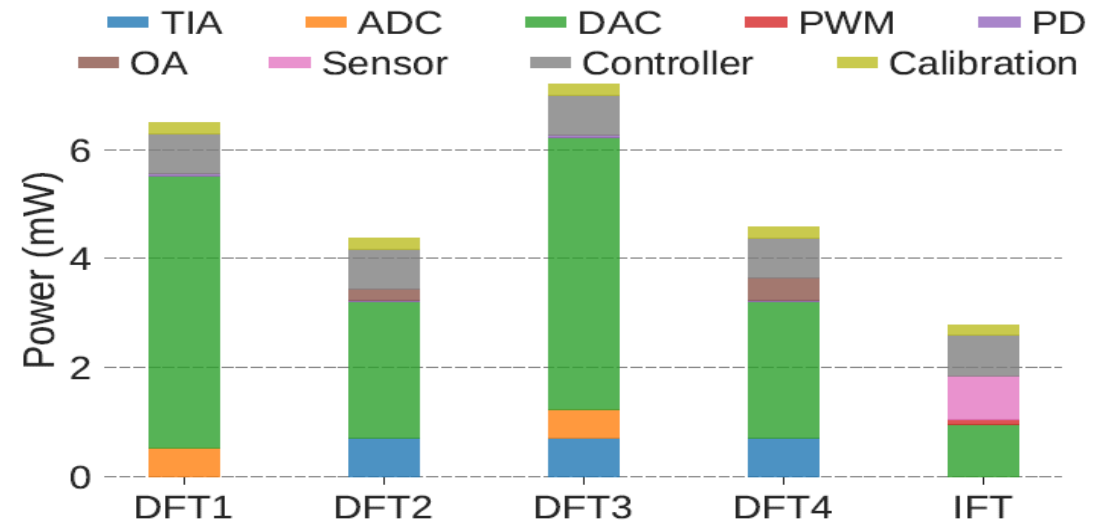
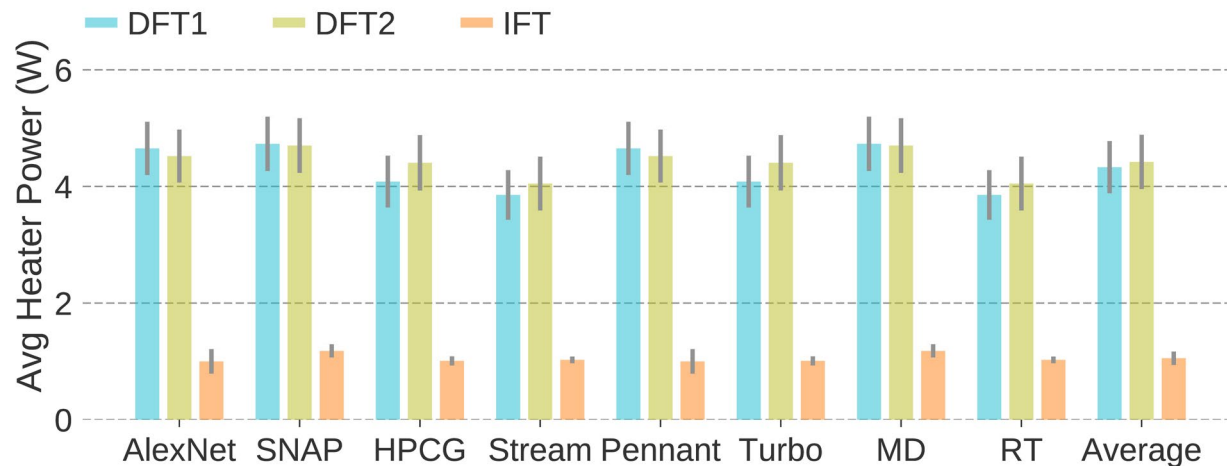
Bit Error Rate

- IFT can achieve BER better than 10^{-9}
 - Based on the simulation results under COSMIC benchmark suite
- IFT shows $10^5 \sim 10^8$ improvement over other methods
- IFT is robust under process variations



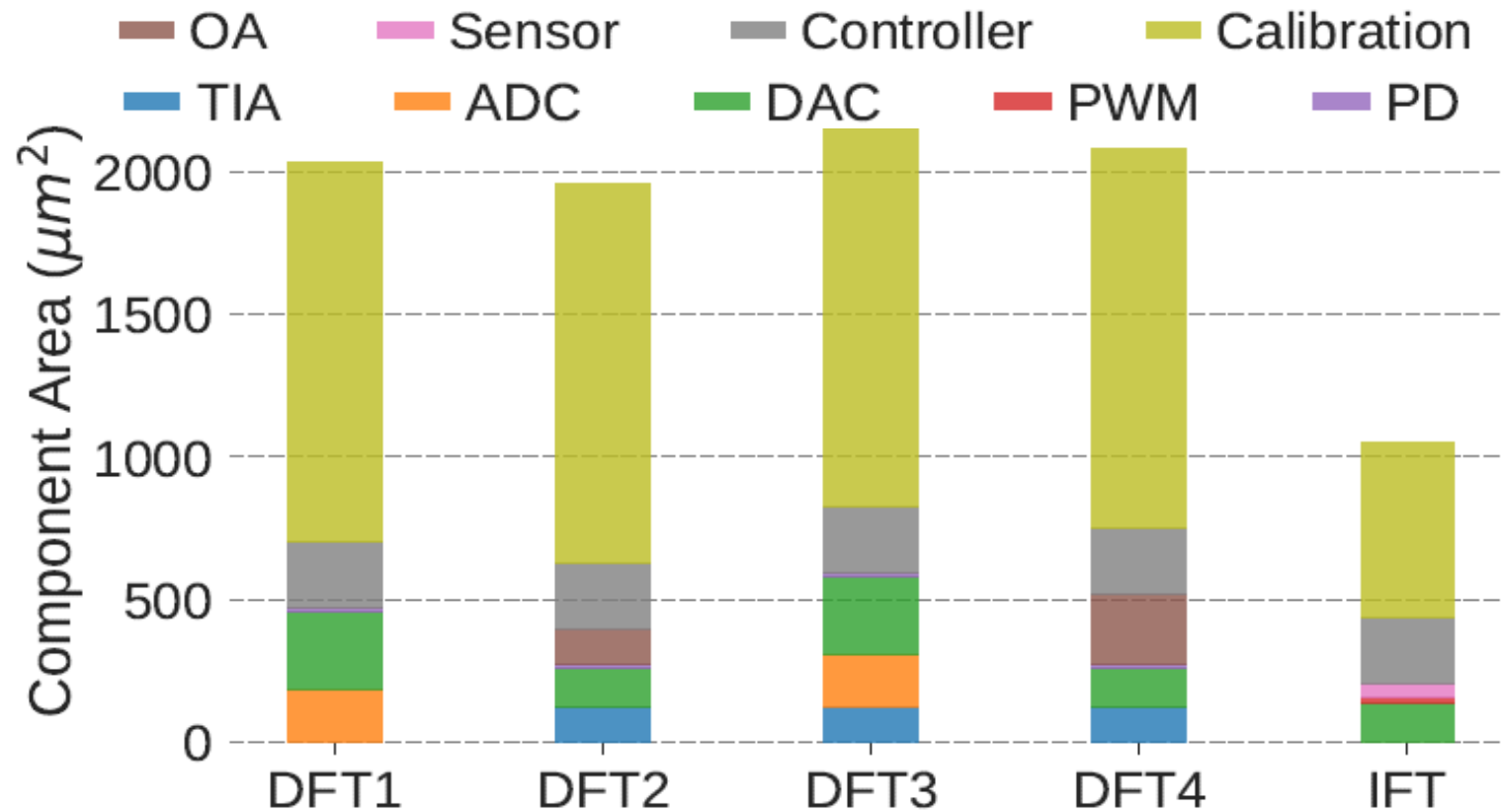
Power Overhead

- Dominated by heater power
- IFT is up to 4X more power efficient than other methods
- IFT is more robust under process variations than other methods



Area Overhead

- IFT is up to 51% smaller than other methods



Reference

- [1] M. Pantouvaki et al., “Active components for 50 Gb/s NRZ-OOK optical interconnects in a silicon photonics platform,” JLT, 2017.
- [2] M. Rakowski, “Silicon photonics platform for 50G optical interconnects,” in PSW, 2017.
- [3] J. Sun et al., “A 128 Gb/s PAM4 Silicon Microring Modulator,” in OFC, 2018.
- [4] J. B. Driscoll et al., “First 400G 8-Channel CWDM Silicon Photonic Integrated Transmitter,” in GFP, 2018.
- [5] Z. Wang et al., “High-Radix Nonblocking Integrated Optical Switching Fabric for Data Center,” JLT, 2017.
- [6] Y. Shen et al., “Deep learning with coherent nanophotonic circuits,” Nature photonics, 2017.
- [7] J. Teng et al., “Athermal Silicon-on-insulator ring resonators by overlaying a polymer cladding on narrowed waveguides,” Optics express, 2009.
- [8] B. Guha et al., “Athermal silicon microring resonators with titanium oxide cladding,” Optics express, 2013.
- [9] X. Xiao et al., “25 Gbit/s silicon microring modulator based on misalignment-tolerant interleaved PN junctions,” Optics express, 2012.
- [10] J. C. Rosenberg et al., “A 25 Gbps silicon microring modulator based on an interleaved junction,” Optics express, 2012.
- [11] D. MarrisMorini et al., “Low loss 40 Gbit/s silicon modulator based on interleaved junctions and fabricated on 300 mm SOI wafers,” Optics express, 2013.
- [12] M. Georgas et al., “A monolithically-integrated optical transmitter and receiver in a zero-change 45nm SOI process,” in VLSIC, 2014.
- [13] Y. Thonnart et al., “A 10Gb/s Si-photonics transceiver with 150μW 120ms-lock-time digitally supervised analog microring wavelength stabilization for 1Tb/s/mm² Die-to-Die Optical Networks,” in ISSCC, 2018.
- [14] C. Li et al., “Silicon photonic transceiver circuits with microring resonator bias-based wavelength stabilization in 65 nm CMOS,” JSSC, 2014.
- [15] K. Yu et al., “22.4 A 24Gb/s 0.71pJ/b Si-photonics source-synchronous receiver with adaptive equalization and microring wavelength stabilization,” in ISSCC, 2015.
- [16] H. Li et al., “22.6 A 25Gb/s 4.4V-swing AC-coupled Si-photonics microring transmitter with 2-tap asymmetric FFE and dynamic thermal tuning in 65nm CMOS,” in ISSCC, 2015.
- [17] C. Sun et al., “A 45 nm CMOS-SOI Monolithic Photonics Platform With Bit-Statistics-Based Resonant Microring Thermal Tuning,” JSSC, 2016.
- [18] R. Wu et al., “Variation-Aware Adaptive Tuning for Nanophotonic Interconnects,” in ICCAD, 2015.
- [19] A. Qouneh et al., “Aurora: A thermally resilient photonic network-on-chip architecture,” in ICCD, 2012.
- [20] Z. Zhang et al., “A Learning-Based Thermal-Sensitive Power Optimization Approach for Optical NoCs,” JETC, 2018.
- [21] Y. Xu et al., “Tolerating Process Variations in Nanophotonic On-chip Networks,” in ISCA, 2012.
- [22] Y. Ye et al., “System-Level Modeling and Analysis of Thermal Effects in WDM-Based Optical Networks-on-Chip,” TCAD, 2014.
- [23] T. Zhang et al., “Thermal management of manycore systems with silicon-photonics networks,” in DATE, 2014.
- [24] C. J. Nitta et al., “Resilient microring resonator based photonic networks,” in MICRO, 2011.
- [25] Z. Li et al., “Reliability modeling and management of nanophotonic on-chip networks,” TVLSI, 2012.
- [26] M. Mohamed et al., “Reliability-Aware Design Flow for Silicon Photonics On-Chip Interconnect,” TVLSI, 2014.
- [27] J. L. Abellan et al., “Adaptive Tuning of Photonic Devices in a Photonic NoC Through Dynamic Workload Allocation,” TCAD, 2016.
- [28] P. Yang et al., “Multi-Domain Inter/Intra-Chip Silicon Photonic Networks for Energy-Efficient Rack-Scale Computing Systems,” TCAD, 2019.
- [29] M. Bahadori et al., “Thermal Rectification of Integrated Microheaters for Microring Resonators in Silicon Photonics Platform,” JLT, 2018.
- [30] H. Li et al., “Thermal aware design method for VCSEL-based on-chip optical interconnect,” in DATE, 2015.
- [31] C. Sun et al., “A 45nm SOI monolithic photonics chip-to-chip link with bit-statistics-based resonant microring thermal tuning,” in VLSIC, 2015.
- [32] E. Timurdogan et al., “Automated wavelength recovery for microring resonators,” in CLEO, 2012.
- [33] K. Padmaraju et al., “Thermal stabilization of a microring modulator using feedback control,” Optics express, 2012.
- [34] D. Ding et al., “GLOW: A global router for low-power thermal-reliable interconnect synthesis using photonic wavelength multiplexing,” in ASP-DAC, 2012.
- [35] H. Jayatileka et al., “Automatic Configuration and Wavelength Locking of Coupled Silicon Ring Resonators,” JLT, 2018.
- [36] Y. Demir et al., “Parka: Thermally Insulated Nanophotonic Interconnects,” in tISNC, 2015.
- [37] X. Chen et al., “Modeling and Analysis of Optical Modulators Based on Free-Carrier Plasma Dispersion Effect,” TCAD, 2019.
- [38] S. K. Selvaraja et al., “Subnanometer Linewidth Uniformity in Silicon Nanophotonic Waveguide Devices Using CMOS Fabrication Technology,” JSTQE, 2010.
- [39] A. E. Lim et al., “Review of Silicon Photonics Foundry Efforts,” JSTQE, 2014.
- [40] N. Drego et al., “Lack of Spatial Correlation in MOSFET Threshold Voltage Variation and Implications for Voltage Scaling,” TSM, 2009.
- [41] F. Horikiri et al., “Wafer-Level Donor Uniformity Improvement by Substrate Off-Angle Control for Vertical GaN-on-GaN Power Switching Devices,” TSM, 2017.
- [42] P. Chen et al., “A time-to-digital-converter-based CMOS smart temperature sensor,” JSSC, 2005.
- [43] M. A. Pertijs et al., “A CMOS smart temperature sensor with a 3σ inaccuracy of 0.1 °C from -55 °C to 125 °C,” JSSC, 2005.
- [44] K. Souri et al., “A CMOS Temperature Sensor With a Voltage-Calibrated Inaccuracy of 0.15 °C (3σ) from -55 °C to 125 °C,” JSSC, 2013.
- [45] W. Huang et al., “HotSpot: A compact thermal modeling methodology for early-stage VLSI design,” TVLSI, 2006.
- [46] M. Rakowski et al., “22.5 A 4 20Gb/s WDM ring-based hybrid CMOS silicon photonics transceiver,” in ISSCC, 2015.
- [47] X. Wu et al., “SUOR: Sectioned Undirectional Optical Ring for Chip Multiprocessor,” JETC, 2014.
- [48] A. V. Krishnamoorthy et al., “Progress in low-power switched optical interconnects,” JSTQE, 2011.
- [49] G. Masini et al., “A four-channel, 10 Gbps monolithic optical receiver in 130nm CMOS with integrated Ge waveguide photodetectors,” in NFOEC, 2007.
- [50] F. Y. Liu et al., “10-Gbps, 5.3-mW Optical Transmitter and Receiver Circuits in 40-nm CMOS,” JSSC, 2012.
- [51] R. K. V. Maeda et al., “JADE: A Heterogeneous Multiprocessor System Simulation Platform Using Recorded and Statistical Application Models,” in AISTECS, 2016.
- [52] S. Li et al., “McPAT: An Integrated Power, Area, and Timing Modeling Framework for Multicore and Manycore Architectures,” in MICRO, 2009.
- [53] “APEX benchmark,” <http://www.nersc.gov/research-and-development/apex/apex-benchmarks>

Thanks!

